

radiating rays passing to the region irradiated through the opening generate the crystal defects within the region irradiated.

10. (New) The semiconductor device in accordance with Claim 9, wherein the metal wiring layer is formed in a thickness so as to restrict penetration of the radiating rays into the region irradiated.

11. (New) The semiconductor device in accordance with Claim 10, wherein an insulating layer is formed above the region irradiated, the opening being on the insulating layer.

12. (New) The semiconductor device in accordance with Claim 11, wherein the metal wiring layer covers a part of the insulating layer.

13. (New) The semiconductor device in accordance with Claim 12, wherein the semiconductor device is an insulated gate bipolar transistor, and wherein the region irradiated is a positive-negative junction where a parasitic diode is generated.

14. (New) The semiconductor device in accordance with Claim 12, wherein the semiconductor device is a metal oxide semiconductor field effect transistor, and wherein the region irradiated is a positive-negative junction region where a parasitic diode is generated.